

## RFP4N100, RF1S4N100SM

### 4.3A, 1000V, 3.500 Ohm, High Voltage, N-Channel Power MOSFETs

The RFP4N100 and RFP4N100SM are N-Channel enhancement mode silicon gate power field effect transistors. They are designed for use in applications such as switching regulators, switching converters, motor drivers, relay drivers, and drivers for high power bipolar switching transistors requiring high speed and low gate drive power. This type can be operated directly from an integrated circuit.

### Features

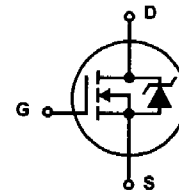
- 4.3A, 1000V
- $r_{DS(ON)} = 3.500\Omega$
- UIS Rating Curve (Single Pulse)
- -55°C to 150°C Operating Temperature

### Ordering Information

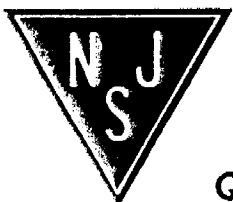
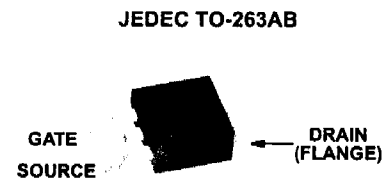
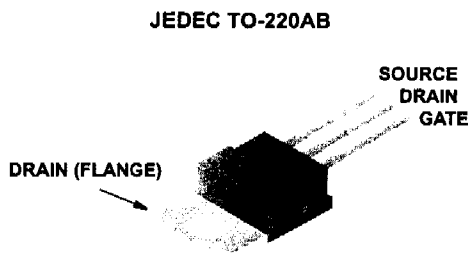
PART NUMBER	PACKAGE	BRAND
RFP4N100	TO-220AB	RFP4N100
RF1S4N100SM	TO-263AB	F1S4N100

NOTE: When ordering, use the entire part number.

### Symbol



### Packaging



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

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## RFP4N100, RF1S4N100SM

### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ , Unless Otherwise Specified

	RFP4N100, RF1S4N100SM	UNITS
Drain to Source Breakdown Voltage (Note 1) . . . . .	1000	V
Drain to Gate Voltage ( $R_{GS} = 20k\Omega$ ) (Note 1) . . . . .	1000	V
Continuous Drain Current . . . . .	4.3	A
Pulsed Drain Current (Note 3) . . . . .	17	A
Gate to Source Voltage . . . . .	$\pm 20$	V
Single Pulse Avalanche Rating . . . . .	(See UIS SOA Curve) (Figures 4, 14, 15)	mJ
Maximum Power Dissipation . . . . .	150	W
Linear Derating Factor . . . . .	1.2	$W/^\circ\text{C}$
Operating and Storage Temperature . . . . .	$-55$ to $150$	$^\circ\text{C}$
Maximum Temperature for Soldering		
Leads at 0.063in (1.6mm) from case for 10s . . . . .	$T_L$ 300	$^\circ\text{C}$
Package Body for 10s, see Techbrief 334 . . . . .	$T_{pkg}$ 260	$^\circ\text{C}$

**CAUTION:** Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

**NOTE:**

1.  $T_J = 25^\circ\text{C}$  to  $125^\circ\text{C}$ .

### Electrical Specifications $T_C = 25^\circ\text{C}$ , Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Drain to Source Breakdown Voltage	$BV_{DSS}$	$I_D = 250\mu\text{A}$ , $V_{GS} = 0\text{V}$ (Figure 10)	1000	-	-	V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$ , $I_D = 250\mu\text{A}$	2	-	4	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 1000\text{V}$ , $V_{GS} = 0\text{V}$	-	-	25	$\mu\text{A}$
		$V_{DS} = 800\text{V}$ , $V_{GS} = 0\text{V}$ , $T_C = 150^\circ\text{C}$	-	-	100	$\mu\text{A}$
Gate to Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20\text{V}$	-	-	$\pm 100$	nA
Drain to Source On Resistance (Note 2)	$r_{DS(ON)}$	$I_D = 2.5\text{A}$ , $V_{GS} = 10\text{V}$ (Figures 8, 9)	-	-	3.500	$\Omega$
Turn-On Delay Time	$t_{d(ON)}$	$V_{DD} = 500\text{V}$ , $I_D = 3.9\text{A}$ , $R_{GS} = 9.1\Omega$ , $R_L = 120\Omega$	-	-	30	ns
Rise Time	$t_r$		-	-	50	ns
Turn-Off Delay Time	$t_{d(OFF)}$		-	-	170	ns
Fall Time	$t_f$		-	-	50	ns
Total Gate Charge (Gate to Source + Gate to Drain)	$Q_g(TOT)$	$V_{GS} = 20\text{V}$ , $I_D = 3.9\text{A}$ , $V_{DS} = 800\text{V}$ (Figure 13)	-	-	120	nC
Thermal Resistance Junction to Case	$R_{\theta JC}$		-	-	0.83	$^\circ\text{C/W}$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$		-	-	62	$^\circ\text{C/W}$

### Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage	$V_{SD}$	$I_{SD} = 4.3\text{A}$	-	-	1.8	V
Reverse Recovery Time	$t_{rr}$	$I_{SD} = 3.9\text{A}$ , $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	1000	ns

**NOTES:**

2. Pulse test: pulse width  $\leq 80\mu\text{s}$ , duty cycle  $\leq 2\%$ .
3. Repetitive rating: pulse width limited by maximum junction temperature.